TRANSISTOR PLASTIC MEDIUM-POWER SILICON NPN POWER TRANSISTOR

DESCRIPTION

The BD135, BD137 and BD139 are available in TO-126 (SOT32) Package.

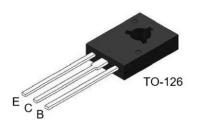
FEATURE

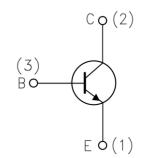
- Complementary with BD136, BD138 and BD140
- Available in TO-126 (SOT32) Package

ORDERING INFORMATION

Package Type	Part Number	
	BD135-6	
	BD135-10	
	BD135-16	
TO 426	BD137-6	
TO-126 (SOT32)	BD137-10	
	BD137-16	
	BD139-6	
	BD139-10	
	BD139-16	
Note	SPQ: 500pcs/Bag	
AiT provides all RoHS Compliant Products		

PIN DESCRIPTION





NPN

PIN#	DESCRIPTION	
1	EMITTER	
2	COLLECTOR	
3	BASE	

h_{FE} TABLE

	BD135-6	BD135-10	BD135-16
Range	BD137-6	BD137-10	BD137-16
	BD139-6	BD139-10	BD139-16
h _{FE}	40~100	63~160	100~250

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ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified

•		
	BD135	45V
BV _{CBO} , Collector-Base Voltage	BD137	60V
	BD139	80V
BV _{CEO} , Collector-Emitter Voltage	BD135	45V
	BD137	60V
	BD139	80V
BV _{EBO} , Emitter-Base Voltage		5V
I _C , Collector Current		1.5A
Pc, Collector Power Dissipation		12.5W
T _{STG} , Storage Temperature		-55°C ∼ + 150°C
T _J , Junction Temperature		+150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

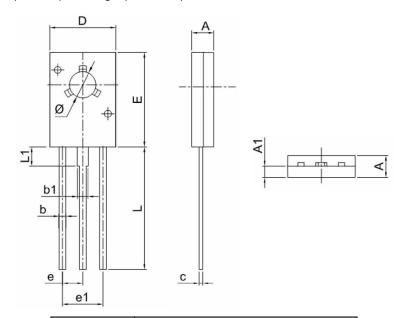
T_A = 25°C, unless otherwise specified

Parameter		Symbol	Conditions	Min.	Тур.	Max.	Unit	
Collector Book	BD135	ВУсво	I _C =100μA, I _E =0	45	-	-	V	
Collector-Base	BD137			60	-	-		
Breakdown Voltage	BD139			80	-	-		
Callantan Funittan	BD135		I _C =10mA, I _B =0	45	-	-	V	
Collector-Emitter	BD137 BVcFo	BVceo		60	-	ı		
Breakdown Voltage	BD139			80	-	ı		
Emitter-Base Breakdov	wn Voltage	BV _{EBO}	I _E =100μA, I _C =0	5		ı	V	
	BD135			-	-	100		
Collector Cut-Off	BD137	Ісво	Ісво	I _{CBO} I _E =0, V _{CB} = 30V	-	-	100	μΑ
Current	BD139			-	-	100		
Emitter Cut-Off Current		I _{EBO}	I _C =0, V _{EB} =5V	-	-	10	μA	
	All Device		I _C =5mA, V _{CE} =2V	25	-	ı		
	All Device		I _C =0.5A, V _{CE} =2V	25	-	ı		
DC Current Gain	BD135	h _{FE}		40		050	-	
	BD137			I _C =150mA, V _{CE} =2V	40	-	250	
	BD139			40	-	160		
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	I _B =50mA, I _C =500mA	-	-	0.5	V	
Base-Emitter Saturation Voltage		V _{BE(ON)}	Ic=0.5A, VcE=2V	-	-	1.0	V	

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PACKAGE INFORMATION

Dimension in TO-126 (SOT32) Package (Unit: mm)



DIM	MILLIMETERS		
DIIVI	MIN	MAX	
Α	2.400	2.800	
A1	1.000	1.400	
b	0.660	0.860	
b1	1.170	1.370	
С	0.400	0.600	
D	7.300	7.700	
E	10.600	11.000	
е	2.250	2.330	
e1	4.500	4.660	
L	14.000	15.000	
L1	1.900	2.500	
Ф	3.100	3.300	

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PLASTIC MEDIUM-POWER SILICON NPN POWER TRANSISTOR

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